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 (Version 7.01 for Windows) now available  
 NEWS 7 AUG 27 BIOCOMMERCE: Changes and enhancements to content coverage  
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 NEWS INTER General Internet Information  
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FILE 'HOME' ENTERED AT 15:24:35 ON 16 NOV 2004

=> file inspec		
COST IN U.S. DOLLARS	SINCE FILE	TOTAL
	ENTRY	SESSION
FULL ESTIMATED COST	0.21	0.21

FILE 'INSPEC' ENTERED AT 15:24:47 ON 16 NOV 2004  
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FILE LAST UPDATED: 15 NOV 2004 <20041115/UP>  
 FILE COVERS 1969 TO DATE.

<<< SIMULTANEOUS LEFT AND RIGHT TRUNCATION AVAILABLE IN  
 THE BASIC INDEX >>>

=> s intrinsic gallium nitride  
 60140 INTRINSIC  
 169893 GALLIUM  
 29974 NITRIDE  
 L1 1 INTRINSIC GALLIUM NITRIDE  
 (INTRINSIC(W)GALLIUM(W)NITRIDE)

=> i ii

L IS NOT A RECOGNIZED COMMAND

The previous command name entered was not recognized by the system.  
For a list of commands available to you in the current file, enter  
"HELP COMMANDS" at an arrow prompt (=>).

=> d ii 1

L1 ANSWER 1 OF 1 INSPEC (C) 2004 IEE on STN

**Full Text** **References**

AN 1996:5330139 INSPEC DN B9609-2810D-002  
TI High field flashover strength of intrinsic gallium nitride and  
aluminum nitride in vacuum.  
AU Khan, M.A.; Chen, O. (APA Opt. Inc., Blaine, MN, USA); Sudarshan, T.S.;  
Gradinaru, G.  
SO Applied Physics Letters (8 July 1996) vol.69, no.2, p.254-6. 17 refs.  
Doc. No.: S0003-6951(96)03128-2  
Published by: AIP  
Price: CCCC 0003-6951/96/69(2)/254/3/\$10.00  
CODEN: APPLAB ISSN: 0003-6951  
SICI: 0003-6951(19960708)69:2L:254:HFFS;1-G  
DT Journal  
TC Experimental  
CY United States  
LA English

=> s semi-insulating gallium nitride

69288 SEMI  
53254 INSULATING  
169893 GALLIUM  
29974 NITRIDE

L2 0 SEMI-INSULATING GALLIUM NITRIDE  
(SEMI(W) INSULATING(W) GALLIUM(W) NITRIDE)

=> s semi insulating gallium nitride

69288 SEMI  
53254 INSULATING  
169893 GALLIUM  
29974 NITRIDE

L3 0 SEMI INSULATING GALLIUM NITRIDE  
(SEMI(W) INSULATING(W) GALLIUM(W) NITRIDE)

=> s semiinsulating gallium nitride

1616 SEMIINSULATING  
169893 GALLIUM  
29974 NITRIDE

L4 0 SEMIINSULATING GALLIUM NITRIDE  
(SEMIINSULATING(W) GALLIUM(W) NITRIDE)

=> log y

COST IN U.S. DOLLARS

SINCE FILE

TOTAL

ENTRY

SESSION

FULL ESTIMATED COST

5.79

6.00

STN INTERNATIONAL LOGOFF AT 15:26:24 ON 16 NOV 2004

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 Patent Office Classifications  
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 MACINTOSH VERSION IS V6.0c(ENG) AND V6.0Jc(JP),  
 AND CURRENT DISCOVER FILE IS DATED 11 AUGUST 2004

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=> file inspec

COST IN U.S. DOLLARS

SINCE FILE  
ENTRY

TOTAL  
SESSION

FULL ESTIMATED COST

0.21

0.21

FILE 'INSPEC' ENTERED AT 17:18:19 ON 16 NOV 2004

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FILE LAST UPDATED: 15 NOV 2004

&lt;20041115/UP&gt;

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<<< SIMULTANEOUS LEFT AND RIGHT TRUNCATION AVAILABLE IN  
THE BASIC INDEX >>>

=&gt; s insulating gan

53254 INSULATING

16401 GAN

L1 63 INSULATING GAN

(INSULATING (W) GAN)

=&gt; s transition metals

381004 TRANSITION

109725 METALS

L2 9497 TRANSITION METALS

(TRANSITION (W) METALS)

=&gt; s l1 and l2

L3 0 L1 AND L2

=&gt; d l1 1-63

L1 ANSWER 1 OF 63 INSPEC (C) 2004 IEE on STN



AN 2004:8130479 INSPEC DN A2004-22-7360L-032; B2004-11-2520D-051

TI Carrier and defect dynamics in photoexcited semi-insulating epitaxial GaN layers.

AU Gaubas, E.; Jursenas, S.; Miasojedovas, S.; Vaitkus, J.; Zukauskas, A.  
(Inst. of Mater. Sci. & Appl. Res., Vilnius Univ., Lithuania)S0 Journal of Applied Physics (15 Oct. 2004) vol.96, no.8, p.4326-33. 22  
refs.

Doc. No.: S0021-8979(04)08919-4

Published by: AIP

Price: CCCC 0021-8979/2004/96(8)/4326(8)/\$22.00

CODEN: JAPIAU ISSN: 0021-8979

SICI: 0021-8979(20041015)96:8L:4326:CDDP;1-Z

DT Journal

TC Theoretical; Experimental

CY United States

LA English

L1 ANSWER 2 OF 63 INSPEC (C) 2004 IEE on STN



AN 2004:8002079 INSPEC DN A2004-15-7360L-003; B2004-08-2550R-001  
 TI Radiation-defect-dependent photoconductivity transients and photoluminescence in semi-insulating GaN.  
 AU Gaubas, E.; Kazlauskas, K.; Tomasiunas, R.; Vaitkus, J.; Zukauskas, A. (Inst. of Mater. Sci. & Appl. Res., Vilnius Univ., Lithuania)  
 SO Applied Physics Letters (21 June 2004) vol.84, no.25, p.5258-60. 12 refs.  
 Doc. No.: S0003-6951(04)03425-4  
 Published by: AIP  
 Price: CCCC 0003-6951/2004/84(25)/5258(3)/\$20.00  
 CODEN: APPLAB ISSN: 0003-6951  
 SIC1: 0003-6951(20040621)84:25L.5258:RDDP;1-Y  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L1 ANSWER 3 OF 63 INSPEC (C) 2004 IEE on STN



AN 2004:7950820 INSPEC DN A2004-12-7360L-001; B2004-06-2550B-012  
 TI Influence of high-temperature annealing on the properties of Fe doped semi-insulating GaN structures.  
 AU Polyakov, A.Y.; Smirnov, N.B.; Govorkov, A.V.; Shlensky, A.A. (Inst. of Rare Metals, Tolmachevsky, Russia); Pearton, S.J.  
 SO Journal of Applied Physics (15 May 2004) vol.95, no.10, p.5591-6. 38 refs.  
 Doc. No.: S0021-8979(04)02510-1  
 Published by: AIP  
 Price: CCCC 0021-8979/2004/95(10)/5591(6)/\$22.00  
 CODEN: JAPIAU ISSN: 0021-8979  
 SIC1: 0021-8979(20040515)95:10L.5591:IHTA;1-K  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L1 ANSWER 4 OF 63 INSPEC (C) 2004 IEE on STN



AN 2004:7926263 INSPEC DN B2004-05-2560S-035  
 TI Enhancement of the electrical properties of AlGaIn/GaN HFETs by using undoped semi-insulating GaN.  
 AU Jeong, Y.H.; Oh, C.S.; Shin, E.H.; Kim, J.Y.; Yang, J.W.; Lim, K.Y. (Dept. of Semicond. Sci. & Technol., Chonbuk Nat. Univ., Chonju, South Korea)  
 SO Journal of the Korean Physical Society (Jan. 2004) vol.44, no.1, p.140-3. 12 refs.  
 Published by: Korean Phys. Soc  
 CODEN: KPSJAS ISSN: 0374-4884  
 SIC1: 0374-4884(200401)44:1L.140:EEPA;1-R  
 Conference: 10th Korean Conference on Semiconductors. Seoul, South Korea,

27-28 Feb 2003

DT Conference Article; Journal  
TC Practical; Experimental  
CY Korea, Democratic People's Republic of  
LA English

L1 ANSWER 5 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	References
--------------	------------

AN 2004:7909801 INSPEC DN A2004-09-8115H-015; B2004-05-0520F-004  
TI Growth of semi-**insulating GaN** layer by controlling size of nucleation sites for SAW device applications.  
AU Jae-Hoon Lee; Myoung-Bok Lee; Sung-Ho Hahm; Yong-Hyun Lee; Jung-Hee Lee (Sch. of Electron. Eng. & Comput. Sci., Kyungpook Nat. Univ., Daegu, South Korea); Young-Ho Bae; Hyun Kyung Cho  
S0 MRS Internet Journal of Nitride Semiconductor Research (2003) vol.8S1. 17 refs.  
Collection URL: <http://nsr.mij.mrs.org/>  
Published by: Mater. Res. Soc  
CODEN: MIJNF7 ISSN: 1092-5783  
DT Journal  
TC Practical; Experimental  
CY United States  
LA English

L1 ANSWER 6 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	References
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AN 2004:7903841 INSPEC DN A2004-09-6320P-001  
TI Ro-vibrational modes of H2 in 4H-SiC and 2H-GaN.  
AU Eberlein, T.A.G.; Huggett, L.; Jones, R. (Sch. of Phys., Exeter Univ., UK); Briddon, P.R.  
S0 Physica B (31 Dec. 2003) vol.340-342, p.171-4. 9 refs.  
Published by: Elsevier  
Price: CCCC 0921-4526/2003/\$30.00  
CODEN: PHYBE3 ISSN: 0921-4526  
SICI: 0921-4526(20031231)340/342L:171:VM;1-B  
Conference: 22nd International Conference on Defects in Semiconductors - ICDS-22. Aarhus, Denmark, 28 July-1 Aug 2003  
DT Conference Article; Journal  
TC Theoretical  
CY Netherlands  
LA English

L1 ANSWER 7 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	References
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AN 2004:7855798 INSPEC DN A2004-06-7360L-001; B2004-03-2520D-047  
TI Properties of Fe-doped semi-**insulating GaN** structures.  
AU Polyakov, A.Y.; Smirnov, N.B.; Govorkov, A.V. (Inst. of Rare Metals, Tolmachevsky, Russia); Pearton, S.J.

S0 Journal of Vacuum Science & Technology B (Microelectronics and Nanometer Structures) (Jan. 2004) vol.22, no.1, p.120-5. 37 refs.

Doc. No.: S0734-211X(04)03601-7

Published by: AIP for American Vacuum Soc

Price: CCCC 1071-1023/2004/22(1)/120/6/\$19.00

CODEN: JVTBD9 ISSN: 1071-1023

SICI: 1071-1023(200401)22:1L.120:PDSI;1-4

DT Journal

TC Experimental

CY United States

LA English

L1 ANSWER 8 OF 63 INSPEC (C) 2004 IEE on STN



AN 2004:7821192 INSPEC DN A2004-03-6630J-005

TI Hydrogen molecules in 4H-SiC and 2H-GaN.

AU Eberlein, T.A.G.; Huggett, L.; Jones, R. (Sch. of Phys., Exeter Univ., UK); Briddon, P.R.

S0 Journal of Physics: Condensed Matter (8 Oct. 2003) vol.15, no.39, p.S2897-902. 11 refs.

Doc. No.: S0953-8984(03)67271-1

Published by: IOP Publishing

Price: CCCC 0953-8984/03/392897+06\$30.00

CODEN: JCOMEL ISSN: 0953-8984

SICI: 0953-8984(20031008)15:39L.s2897:HM;1-A

Conference: Workshop on 'Physics of Group IV Materials'. Exeter, UK, 7-10 April 2003

DT Conference Article; Journal

TC Theoretical

CY United Kingdom

LA English

L1 ANSWER 9 OF 63 INSPEC (C) 2004 IEE on STN



AN 2003:7770510 INSPEC DN A2003-24-7360L-001; B2003-12-2520D-019

TI Electrical and optical properties of Fe-doped semi-insulating GaN templates.

AU Polyakov, A.Y.; Smirnov, N.B.; Govorkov, A.V. (Inst. of Rare Metals, Moscow, Russia); Pearton, S.J.

S0 Applied Physics Letters (20 Oct. 2003) vol.83, no.16, p.3314-16. 20 refs.

Doc. No.: S0003-6951(03)05042-3

Published by: AIP

Price: CCCC 01/03/6951/2003/83(16)/3314(3)/\$20.00

CODEN: APPLAB ISSN: 0003-6951

SICI: 0003-6951(20031020)83:16L.3314:EOPD;1-1

DT Journal

TC Experimental

CY United States

LA English

L1 ANSWER 10 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2003:7756693 INSPEC DN A2003-23-8115H-005; B2003-11-0520F-075  
 TI Role of potential barriers in epitaxial layers of semi-insulating GaN layers.  
 AU Vaitkus, J.V.; Gaubas, E. (Inst. of Mater. Sci. & Appl. Res., Vilnius Univ., Lithuania); Sakai, S.; Lacroix, Y.; Tao Wang; Smith, K.M.; Rahman, M.; Cunningham, W.  
 SO Diffusion and Defect Data Part B (Solid State Phenomena) (2003) vol.93, p.301-6. 12 refs.  
 Published by: Balaban Publishers; Scitec Publications  
 CODEN: DDBPE8 ISSN: 1012-0394  
 SICI: 1012-0394(2003)93L:301:RPBE;1-Y  
 DT Journal  
 TC Experimental  
 CY Switzerland  
 LA English

L1 ANSWER 11 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2003:7741695 INSPEC DN A2003-21-7220P-002  
 TI Thermoelectric effect spectroscopy measurements on semi-insulating GaN.  
 AU Pavlovic, M.; Desnica, U.V. (Ruder Boskovic Inst., Zagreb, Croatia); Fang, Z.-Q.; Look, D.C.  
 SO Vacuum (9 May 2003) vol.71, no.1-2, p.153-8. 28 refs.  
 Published by: Elsevier  
 Price: CCCC 0042-207X/03/\$30.00  
 CODEN: VACUAV ISSN: 0042-207X  
 SICI: 0042-207X(20030509)71:1/2L:153:TESM;1-R  
 Conference: 9th Joint Vacuum Conference (JVC-9). Schloss Seggau, Austria, 16-20 June 2002  
 DT Conference Article; Journal  
 TC Experimental  
 CY United Kingdom  
 LA English

L1 ANSWER 12 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2003:7728893 INSPEC DN A2003-20-7320D-040; B2003-10-2520D-045  
 TI Two-dimensional electron gases induced by polarization charges in AlN/GaN heterostructure grown by plasma-assisted molecular-beam epitaxy.  
 AU Jeganathan, K.; Ide, T.; Shimizu, M.; Okumura, H. (Power Electron. Res. Center, Nat. Inst. of Adv. Ind. Sci. & Technol., Ibaraki, Japan)  
 SO Journal of Applied Physics (1 Sept. 2003) vol.94, no.5, p.3260-3. 18 refs.  
 Doc. No.: S0021-8979(03)07218-9  
 Published by: AIP  
 Price: CCCC 0021-8979/2003/94(5)/3260(4)/\$20.00



CODEN: JAPIAU ISSN: 0021-8979  
SICI: 0021-8979(20030901)94:5L:3260:DEGI;1-R

DT Journal  
TC Experimental  
CY United States  
LA English

L1 ANSWER 13 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Cited References
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AN 2003:7723750 INSPEC DN A2003-20-7860H-005; B2003-10-4220-016  
TI Luminescence properties of charged dislocations in semi-insulating GaN:Zn.  
AU Srinivasan, S.; Cai, J.; Contreras, O.; Ponce, F.A. (Dept. of Phys. &  
Astron., Arizona State Univ., Tempe, AZ, USA); Look, D.C.; Molnar, R.J.  
S0 Physica Status Solidi C (2002) no.1, p.508-11. 7 refs.  
Published by: Wiley-VCH  
Price: CCCC 1610-1634/02/00012-0508\$17.50+.50/0  
CODEN: PSSCGL ISSN: 1610-1634  
SICI: 1610-1634(2002)1L:508:LPCD;1-G  
Conference: International Workshop on Nitride Semiconductors (IWN 2002).  
Aachen, Germany, 22-25 July 2002

DT Conference Article; Journal  
TC Experimental  
CY Germany, Federal Republic of  
LA English

L1 ANSWER 14 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Cited References
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AN 2003:7653110 INSPEC DN A2003-14-7240-011; B2003-07-4210-017  
TI Deep-defect-induced quenching effects in semi-insulating GaN layers  
detected by photoelectrical spectroscopic techniques.  
AU Witte, H.; Krtschil, A.; Lisker, M.; Schrenk, E.; Christen, J.; Krost, A.  
(Inst. of Exp. Phys., Otto-von-Guericke-Univ., Magdeburg, Germany); Kuhn,  
B.; Scholz, F.  
S0 Applied Physics Letters (9 June 2003) vol.82, no.23, p.4083-5. 16 refs.  
Published by: AIP  
Price: CCCC 01/03/6951/2003/82(23)/4083(3)/\$20.00  
CODEN: APPLAB ISSN: 0003-6951  
SICI: 0003-6951(20030609)82:23L:4083:DDIQ;1-V

DT Journal  
TC Experimental  
CY United States  
LA English

L1 ANSWER 15 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Cited References
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AN 2003:7650116 INSPEC DN B2003-07-0520F-069  
TI Engineering of an insulating buffer and use of AlN interlayers: two  
optimisations for AlGaIn-GaN HEMT-like structures.

AU Bougrioua, Z. (CRHEA, CNRS, Valbonne, France); Moerman, I.; Nistor, L.;  
Van Daele, B.; Monroy, E.; Palacios, T.; Calle, F.; Leroux, M.  
S0 Physica Status Solidi C (2003) no.3, p.93-100. 12 refs.  
Published by: Wiley-VCH  
Price: CCCC 0031-8965/03/19501-0093\$17.50+.50/0  
ISSN: 1610-1634  
SICI: 1610-1634(2003)3L:93:EIBI;1-0  
DT Journal  
TC Practical; Experimental  
CY Germany, Federal Republic of  
LA English

L1 ANSWER 16 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2003:7583016 INSPEC DN A2003-10-7125T-005; B2003-05-2520D-046  
TI The franz-keldysh effect in shocked GaN:Mg.  
AU Peng, H.Y.; McCluskey, M.D.; Gupta, Y.M. (Dept. of Phys., Washington State  
Univ., Pullman, WA, USA); Kneissl, M.; Johnson, N.M.  
S0 Applied Physics Letters (31 March 2003) vol.82, no.13, p.2085-7. 23 refs.  
Published by: AIP  
Price: CCCC 01/03/6951/2003/82(13)/2085(3)/\$19.00  
CODEN: APPLAB ISSN: 0003-6951  
SICI: 0003-6951(20030331)82:13L:2085:FKES;1-I  
DT Journal  
TC Experimental  
CY United States  
LA English

L1 ANSWER 17 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2003:7562747 INSPEC DN A2003-09-6855-004; B2003-04-2520D-063  
TI Growth of Fe doped semi-insulating GaN by metalorganic chemical vapor  
deposition.  
AU Heikman, S.; Keller, S.; DenBaars, S.P.; Mishra, U.K. (Dept. of Electr. &  
Comput. Eng., California Univ., Santa Barbara, CA, USA)  
S0 Applied Physics Letters (15 July 2002) vol.81, no.3, p.439-41. 28 refs.  
Doc. No.: S0003-6951(02)01826-0  
Published by: AIP  
Price: CCCC 01/03/6951/2002/81(3)/439(3)/\$19.00  
CODEN: APPLAB ISSN: 0003-6951  
SICI: 0003-6951(20020715)81:3L:439:GDSI;1-T  
DT Journal  
TC Experimental  
CY United States  
LA English

L1 ANSWER 18 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2003:7555977 INSPEC DN A2003-08-7855-037  
 TI Annealing effect on the Al<sup>+</sup> implantation induced deep traps in GaN film.  
 AU Xu Xiao-liang; He Hai-yan; Liu Hong-tu; Shi Chao-shu (Struct. Res. Lab., Univ. of Sci. & Technol. of China, Hefei, China); Ge Wei-kun; Luo, E. Z.; Sundaravel, B.; Wilson, I. H.  
 SO Chinese Journal of Liquid Crystals and Displays (Aug. 2002) vol.17, no.4, p.243-52. 22 refs.  
 Published by: Science Press  
 ISSN: 1007-2780  
 SICI: 1007-2780(200208)17:4L.243:AEII;1-8  
 DT Journal  
 TC Experimental  
 CY China  
 LA Chinese

L1 ANSWER 19 OF 63 INSPEC (C) 2004 IEE on STN



AN 2003:7501464 INSPEC DN A2003-04-6855-046; B2003-02-2560S-018  
 TI Comparison of high mobility AlGa<sub>N</sub>/Ga<sub>N</sub> heterostructures grown by MBE on HVPE Ga<sub>N</sub> templates and directly nucleated on sapphire.  
 AU Manfra, M. J.; Weimann, N. G.; Hsu, J. W. P.; Pfeiffer, L. N.; West, K. W. (Lucent Technol. Bell Labs., Murray Hill, NJ, USA); Molnar, R. J.  
 SO 2002 International Conference on Molecular Beam Epitaxy (Cat. No.02EX607) Piscataway, NJ, USA: IEEE, 2002. p.231-2 of 424 pp.  
 Conference: San Francisco, CA, USA, 15-20 Sept 2002  
 Sponsor(s): IEEE Lasers & Electro-Opt. Soc  
 Price: CCCC 0-7803-7581-5/02/\$17.00  
 ISBN: 0-7803-7581-5  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L1 ANSWER 20 OF 63 INSPEC (C) 2004 IEE on STN



AN 2003:7490791 INSPEC DN A2003-03-7240-006; B2003-02-4210-007  
 TI Photo-stimulated current spectroscopy and its application in detecting aluminum implantation-induced deep traps in Ga<sub>N</sub>.  
 AU Xiaoliang Xu; Haiyan He; Hongtu Liu; Chaoshu Shi (Struct. Res. Lab., Acad. Sinica, Hefei, China); Weikun Ge; Luo, E. Z.; Sundaravel, B.; Wilson, I. H.  
 SO Thin Solid Films (2 Sept. 2002) vol.416, no.1-2, p.294-301. 31 refs.  
 Doc. No.: S0040-6090(02)00681-8  
 Published by: Elsevier  
 Price: CCCC 0040-6090/02/\$22.00  
 CODEN: THSFAP ISSN: 0040-6090  
 SICI: 0040-6090(20020902)416:1/2L.294:PSCS;1-Y  
 DT Journal  
 TC Experimental  
 CY Switzerland

LA English

L1 ANSWER 21 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2002:7453703 INSPEC DN B2002-12-2560S-026  
 TI Characterization of GaN based MESFETs by comparing electroluminescence, photoionization and cathodoluminescence spectroscopy.  
 AU Armani, N. (Ist. MASPEC, CNR, Parma, Italy); Chini, A.; Manfredi, M.; Meneghesso, G.; Pavesi, M.; Grillo, V.; Salviati, G.; Zanoni, E.  
 SO Microscopy of Semiconducting Materials 2001. Proceedings of the Royal Microscopical Society Conference  
 Editor(s): Cullis, A.G.; Hutchinson, J.L.  
 Bristol, UK: IOP Publishing, 2001. p.503-6 of xiv+610 pp. 11 refs.  
 Conference: Oxford, UK, 25-29 March 2001  
 ISBN: 0-7503-0818-4  
 DT Conference Article  
 TC Practical; Experimental  
 CY United Kingdom  
 LA English

L1 ANSWER 22 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2002:7399617 INSPEC DN A2002-22-7155-003; B2002-11-2520D-019  
 TI Thermoelectric effect spectroscopy of deep levels in semi-insulating GaN.  
 AU Desnica, U.V.; Pavlovic, M. (Boskovic (R.) Inst., Zagreb, Croatia); Fang, Z.-Q.; Look, D.C.  
 SO Journal of Applied Physics (1 Oct. 2002) vol.92, no.7, p.4126-8. 28 refs.  
 Doc. No.: S0021-8979(02)08919-3  
 Published by: AIP  
 Price: CCCC 0021-8979/2002/92(7)/4126(3)/\$19.00  
 CODEN: JAPIAU ISSN: 0021-8979  
 SICI: 0021-8979(20021001)92:7L:4126:TESD;1-H  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L1 ANSWER 23 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2002:7383461 INSPEC DN A2002-21-7340L-005; B2002-10-2530B-027  
 TI High mobility AlGaIn/GaN heterostructures grown by plasma-assisted molecular beam epitaxy on semi-insulating GaN templates prepared by hydride vapor phase epitaxy.  
 AU Manfra, M.J.; Weimann, N.G.; Hsu, J.W.P.; Pfeiffer, L.N.; West, K.W. (Lucent Technol. Bell Labs., Murray Hill, NJ, USA); Syed, S.; Stormer, H.L.; Pan, W.; Lang, D.V.; Chu, S.N.G.; Kowach, G.; Sergeant, A.M.; Caissie, J.; Molvar, K.M.; Mahoney, L.J.; Molnar, R.J.  
 SO Journal of Applied Physics (1 July 2002) vol.92, no.1, p.338-45. 15 refs.

Doc. No. : S0021-8979(02)03414-X  
Published by: AIP  
Price: CCCC 0021-8979/2002/92(1)/338(8)/\$19.00  
CODEN: JAPIAU ISSN: 0021-8979  
SICI: 0021-8979(20020701)92:1L 338:HMAH;1-#

DT Journal  
TC Experimental  
CY United States  
LA English

L1 ANSWER 24 OF 63 INSPEC (C) 2004 IEE on STN



AN 2002:7380070 INSPEC DN A2002-21-7865K-006; B2002-10-2520D-049  
TI Optical metastability in undoped GaN grown on Ga-rich GaN buffer layers.  
AU Dhar, S.; Ghosh, S. (Sch. of Phys. Sci., Jawaharlal Nehru Univ., New Delhi, India)  
S0 Applied Physics Letters (17 June 2002) vol.80, no.24, p.4519-21. 24 refs.  
Doc. No. : S0003-6951(02)06221-6  
Published by: AIP  
Price: CCCC 0003-6951/2002/80(24)/4519(3)/\$19.00  
CODEN: APPLAB ISSN: 0003-6951  
SICI: 0003-6951(20020617)80:24L 4519:OMUG;1-I

DT Journal  
TC Experimental  
CY United States  
LA English

L1 ANSWER 25 OF 63 INSPEC (C) 2004 IEE on STN



AN 2002:7367591 INSPEC DN A2002-20-8115G-008; B2002-10-2530B-006  
TI Dislocation and morphology control during molecular-beam epitaxy of AlGaIn/GaN heterostructures directly on sapphire substrates.  
AU Manfra, M.J.; Weimann, N.G.; Hsu, J.W.P.; Pfeiffer, L.N.; West, K.W. (Lucent Technol. Bell Labs., Murray Hill, NJ, USA); Chu, S.N.G.  
S0 Applied Physics Letters (19 Aug. 2002) vol.81, no.8, p.1456-8. 9 refs.  
Doc. No. : S0003-6951(02)04731-9  
Published by: AIP  
Price: CCCC 0003-6951/2002/81(8)/1456(3)/\$19.00  
CODEN: APPLAB ISSN: 0003-6951  
SICI: 0003-6951(20020819)81:8L 1456:DMCD;1-2

DT Journal  
TC Experimental  
CY United States  
LA English

L1 ANSWER 26 OF 63 INSPEC (C) 2004 IEE on STN



AN 2002:7348972 INSPEC DN A2002-18-7865K-045

TI Optical study of GaN doped with Mn grown by metal organic vapor phase epitaxy.  
 AU Korotkov, R.Y.; Gregie, J.M.; Wessels, B.W. (Dept. of Mater. Sci. & Eng., Northwestern Univ., Evanston, IL, USA)  
 SO GaN and Related Alloys - 2000. Symposium (Materials Research Society Symposium Proceedings Vol.639)  
 Editor(s): Wetzol, C.; Shur, M.S.; Mishra, U.K.; Gil, B.; Kishino, K.  
 Warrendale, PA, USA: Mater. Res. Soc, 2001. p.G3.7.1-6 of xxvii+938 pp. 19 refs.  
 Conference: Boston, MA, USA, 27 Nov-1 Dec 2000  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L1 ANSWER 27 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2002:7166632 INSPEC DN A2002-05-7340L-014; B2002-03-2560S-010  
 TI Back bias effects in AlGaIn/GaN HFETs.  
 AU Uren, M.J.; Herbert, D.; Martin, T.; Hughes, B.T.; Birbeck, J.; Balmer, R.; Pidduck, A.J. (QinetiQ Ltd., Malvern, UK); Jones, S.K.  
 SO Physica Status Solidi A (16 Nov. 2001) vol.188, no.1, p.195-8. 10 refs.  
 Published by: Wiley-VCH  
 Price: CCCC 0031-8965/01/18811-0195\$17.50+.50/0  
 CODEN: PSSABA ISSN: 0031-8965  
 SIC1: 0031-8965(20011116)188:1L.195:BBA;1-7  
 Conference: Fourth International Conference on Nitride Semiconductors.  
 Denver, CO, USA, 16-20 July 2001  
 DT Conference Article; Journal  
 TC Practical; Experimental  
 CY Germany, Federal Republic of  
 LA English

L1 ANSWER 28 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 2002:7159990 INSPEC DN A2002-05-8115G-012; B2002-02-0520D-053  
 TI Growth and characterisation of high electron mobility transistors on 4H-SiC by ammonia molecular beam epitaxy.  
 AU Webb, J.; Haipeng Tang; Bardwell, J.A.; Rolfe, S.; Ying Liu; Lapointe, A.; Marshall, P. (Inst. for Microstructural Sci., Nat. Res. Council of Canada, Ottawa, Ont., Canada); MacElwee, T.W.  
 SO Physica Status Solidi A (16 Nov. 2001) vol.188, no.1, p.271-4. 9 refs.  
 Published by: Wiley-VCH  
 Price: CCCC 0031-8965/01/18811-0271\$17.50+.50/0  
 CODEN: PSSABA ISSN: 0031-8965  
 SIC1: 0031-8965(20011116)188:1L.271:GCHE;1-Q  
 Conference: Fourth International Conference on Nitride Semiconductors.  
 Denver, CO, USA, 16-20 July 2001  
 DT Conference Article; Journal

TC Experimental  
CY Germany, Federal Republic of  
LA English

L1 ANSWER 29 OF 63 INSPEC (C) 2004 IEE on STN



AN 2002:7143723 INSPEC DN A2002-04-7320D-011; B2002-02-2530B-020  
TI 2DEG characteristics of AlN/GaN heterointerface on sapphire substrates grown by plasma-assisted MBE.  
AU Jeganathan, K.; Ide, T.; Shen, S.X.Q.; Shimizu, M.; Okumura, H. (Power Electron. Res. Center, Nat. Inst. of Adv. Ind. Sci. & Technol., Ibaraki, Japan)  
S0 Physica Status Solidi B (1 Nov. 2001) vol.228, no.2, p.613-16. 17 refs. Published by: Wiley-VCH  
Price: CCCC 0370-1972/01/22811-0613\$17.50+.50/0  
CODEN: PSSBBD ISSN: 0370-1972  
SICI: 0370-1972(20011101)228:2L;613:2CHS;1-U  
Conference: Fourth International Conference on Nitride Semiconductors. Denver, CO, USA, 16-20 July 2001  
DT Conference Article; Journal  
TC Experimental  
CY Germany, Federal Republic of  
LA English

L1 ANSWER 30 OF 63 INSPEC (C) 2004 IEE on STN



AN 2002:7137121 INSPEC DN B2002-02-2560S-013  
TI Fabrication and characterization of GaN junction field effect transistors.  
AU Zhang, L. (Sandia Nat. Labs., Albuquerque, NM, USA); Lester, L.F.; Baca, A.G.; Shul, R.J.; Chang, P.C.; Willison, C.G.; Mishra, U.K.; Denbaars, S.P.; Zolper, J.C.  
S0 GaN and Related Alloys - 1999. Symposium (Materials Research Society Symposium Proceedings Vol.595)  
Editor(s): Myers, T.H.; Feenstra, R.M.; Shur, M.S.; Amano, H.  
Warrendale, PA, USA: Mater. Res. Soc, 2000. p.W4.9.1-7 of xxvii+10002 pp. 21 refs.  
Conference: Boston, MA, USA, 28 Nov-3 Dec 1999  
ISBN: 1-55899-503-X  
DT Conference Article  
TC Experimental; Practical  
CY United States  
LA English

L1 ANSWER 31 OF 63 INSPEC (C) 2004 IEE on STN



AN 2001:7011094 INSPEC DN A2001-18-6855-086; B2001-09-0520F-088  
TI A single step nucleation process for growth of GaN-based materials by OMVPE.

AU Smart, J.A. (Dept. of Electr. Eng., Cornell Univ., Ithaca, NY, USA);  
Shealy, J.R.  
S0 WOCSDICE 2000. 24th Workshop on Compound Semiconductor Devices and  
Integrated Circuits  
Ann Arbor, MI, USA: Univ. Michigan, 2000. p.1-5, 1-6 of xxii+196 pp. 1  
refs.  
Conference: Aegean Sea, Greece, 29 May-2 June 2000  
ISBN: 0-9703111-0-9  
DT Conference Article  
TC Practical; Experimental  
CY United States  
LA English

L1 ANSWER 32 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Cited References
--------------	---------------------

AN 2001:6991427 INSPEC DN A2001-17-8115G-035; B2001-09-0520D-045  
TI Advances in III-nitride growth by ammonia-MBE.  
AU Webb, J.B.; Tang, H.; Bardwell, J.A. (Inst. for Microstructural Sci., Nat.  
Res. Council of Canada, Ottawa, Ont., Canada)  
S0 Proceedings of International Workshop on Nitride Semiconductors  
Tokyo, Japan: Inst. Pure & Appl. Phys, 2000. p.228-32 of 1002 pp. 9 refs.  
Conference: Nagoya, Japan, 24-27 Sept 2000  
Sponsor(s): Japan Soc. Appl. Phys.; Japan Soc. Promotion of Sci  
ISBN: 4-900526-13-4  
DT Conference Article  
TC General Review; Experimental; Practical  
CY Japan  
LA English

L1 ANSWER 33 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Cited References
--------------	---------------------

AN 2001:6932166 INSPEC DN B2001-07-2560S-001  
TI Effect of growth termination conditions on the performance of AlGaIn/GaN  
high electron mobility transistors.  
AU Keller, S.; Vetury, R.; Parish, G.; DenBaars, S.P.; Mishra, U.K. (Dept.  
Electr. & Comput. Eng., California Univ., Santa Barbara, CA, USA)  
S0 Applied Physics Letters (14 May 2001) vol.78, no.20, p.3088-90. 14 refs.  
Doc. No.: S0003-6951(01)05420-1  
Published by: AIP  
Price: CCCC 0003-6951/2001/78(20)/3088(3)/\$18.00  
CODEN: APPLAB ISSN: 0003-6951  
SICI: 0003-6951(20010514)78:20L:3088:EGTC;1-L  
DT Journal  
TC Experimental  
CY United States  
LA English

L1 ANSWER 34 OF 63 INSPEC (C) 2004 IEE on STN





AN 2000:6795326 INSPEC DN B2001-02-1350F-014  
 TI Recessed-gate GaN MESFET using ICP-RIE for high temperature microwave applications.  
 AU Lee, C.; Lu, W. (Dept. of Electr. & Comput. Eng., Illinois Univ., Urbana, IL, USA); Piner, E.; Adesida, I.  
 SO 58th DRC. Device Research Conference. Conference Digest (Cat. No. 00TH8526) Piscataway, NJ, USA: IEEE, 2000. p.41-2 of xii+176 pp. 6 refs.  
 Conference: Denver, CO, USA, 19-21 June 2000  
 Sponsor(s): IEEE Electron Devices Soc  
 ISBN: 0-7803-6472-4  
 DT Conference Article  
 TC Application; Practical; Experimental  
 CY United States  
 LA English

L1 ANSWER 35 OF 63 INSPEC (C) 2004 FIZ KARLSRUHE on STN



AN 2000:6766620 INSPEC DN A2001-01-7830-012  
 TI Infrared studies on GaN single crystals and homoepitaxial layers.  
 AU Frayssinet, E.; Knap, W. (Groupe d'Etudes des Semicond., CNRS, Montpellier, France); Prystawko, P.; Leszczynski, M.; Grzegory, I.; Suski, T.; Beaumont, B.; Gibart, P.  
 SO Journal of Crystal Growth (Sept. 2000) vol.218, no.2-4, p.161-6. 24 refs.  
 Doc. No.: S0022-0248(00)00537-6  
 Published by: Elsevier  
 Price: CCCC 0022-0248/2000/\$20.00  
 CODEN: JCRGAE ISSN: 0022-0248  
 SICI: 0022-0248(200009)218:2/4L.161:ISSC;1-0  
 DT Journal  
 TC Experimental  
 CY Netherlands  
 LA English

L1 ANSWER 36 OF 63 INSPEC (C) 2004 IEE on STN



AN 2000:6572341 INSPEC DN A2000-11-6855-060; B2000-06-0520J-004  
 TI Near defect free GaN substrates.  
 AU Porowski, S. (High Pressure Res. Center, Acad. of Sci., Warsaw, Poland)  
 SO GaN and Related Alloys. Symposium  
 Editor(s): Pearton, S.J.; Kuo, C.; Wright, A.F.; Uenoyama, T.  
 Warrendale, PA, USA: Mater. Res. Soc, 1999. p.G1.3/11 pp. of 1028 pp. 37 refs.  
 Conference: Boston, MA, USA, 30 Nov-4 Dec 1998  
 ISBN: 1-55899-443-2  
 DT Conference Article  
 TC Experimental  
 CY United States

LA English

L1 ANSWER 37 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Cited References
--------------	---------------------

AN 2000:6540346 INSPEC DN B2000-05-1350F-005

TI Epitaxially-grown GaN junction field effect transistors.

AU Zhang, L. (Sandia Nat. Labs., Albuquerque, NM, USA); Lester, L.F.; Baca, A.G.; Shul, R.J.; Chang, P.C.; Willison, C.G.; Mishra, U.K.; Denbaars, S.P.; Zolper, J.C.

S0 IEEE Transactions on Electron Devices (March 2000) vol. 47, no. 3, p. 507-11. 25 refs.

Doc. No.: S0018-9383(00)01938-9

Published by: IEEE

Price: CCCC 0018-9383/2000/\$10.00

CODEN: IETDAI ISSN: 0018-9383

SICI: 0018-9383(200003)47:3L.507:EGJF;1-4

DT Journal

TC Application; Practical; Experimental

CY United States

LA English

L1 ANSWER 38 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Cited References
--------------	---------------------

AN 1999:6410037 INSPEC DN A2000-01-8115J-001; B2000-01-0520X-001

TI **Insulating GaN:Zn** layers grown by hydride vapor phase epitaxy on SiC substrates.

AU Kuznetsov, N.I.; Nikolaev, A.E.; Zubrilov, A.S. (A.F. Ioffe Physicotech. Inst., Acad. of Sci., St. Petersburg, Russia); Melnik, Yu.V.; Dmitriev, V.A.

S0 Applied Physics Letters (15 Nov. 1999) vol. 75, no. 20, p. 3138-40. 25 refs.

Doc. No.: S0003-6951(99)03446-4

Published by: AIP

Price: CCCC 0003-6951/99/75(20)/3138(3)/\$15.00

CODEN: APPLAB ISSN: 0003-6951

SICI: 0003-6951(19991115)75:20L.3138:ILGH;1-T

DT Journal

TC Experimental

CY United States

LA English

L1 ANSWER 39 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Cited References
--------------	---------------------

AN 1999:6402056 INSPEC DN A1999-24-8115H-014; B1999-12-0520F-095

TI Properties of GaN homoepitaxial layers grown on GaN epitaxial wafers.

AU Dmitriev, V.; Nikolaev, A. (A.F. Ioffe Physicotech. Inst., Acad. of Sci., St. Petersburg, Russia); Cherenkov, A.; Tsvetkov, D.; Stepanov, S.; Kuznetsov, N.; Nikitina, I.; Kovarsky, A.; Yagovkina, M.; Davidov, V.

S0 Wide-Bandgap Semiconductors for High Power, High Frequency and High

Temperature. Symposium

Editor(s): DenBaars, S.; Palmour, J.; Shur, M.; Spencer, M.

Warrendale, PA, USA: Mater. Res. Soc, 1998. p. 451-6 of xiii+565 pp. 14 refs.

Conference: San Francisco, CA, USA, 13-15 April 1998

ISBN: 1-55899-418-1

DT Conference Article

TC Practical; Experimental

CY United States

LA English

L1 ANSWER 40 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	References
--------------	------------

AN 1999:6386564 INSPEC DN A1999-23-0762-006; B1999-12-72300-007

TI The effect of threading dislocations, Mg doping, and etching on the spectral responsivity in GaN-based ultraviolet detectors.

AU Torvik, J.T.; Pankove, J.I. (Astralux Inc., Boulder, CO, USA); Nakamura, S.; Grzegory, I.; Porowski, S.

S0 Journal of Applied Physics (15 Oct. 1999) vol. 86, no. 8, p. 4588-93. 32 refs.

Doc. No.: S0021-8979(99)09820-5

Published by: AIP

Price: CCCC 0021-8979/99/86(8)/4588(6)/\$15.00

CODEN: JAPIAU ISSN: 0021-8979

SICI: 0021-8979(19991015)86:8L.4588:ETDD;1-7

DT Journal

TC Application; Experimental

CY United States

LA English

L1 ANSWER 41 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	References
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AN 1999:6325956 INSPEC DN A1999-19-8115G-001; B1999-10-0520D-001

TI Semi-insulating C-doped GaN and high-mobility AlGaIn/GaN heterostructures grown by ammonia molecular beam epitaxy.

AU Webb, J.B.; Tang, H.; Rolfe, S.; Bardwell, J.A. (Inst. for Microstruct. Sci., Nat. Res. Council of Canada, Ottawa, Ont., Canada)

S0 Applied Physics Letters (16 Aug. 1999) vol. 75, no. 7, p. 953-5. 17 refs.

Doc. No.: S0003-6951(99)00933-X

Published by: AIP

Price: CCCC 0003-6951/99/75(7)/953(3)/\$15.00

CODEN: APPLAB ISSN: 0003-6951

SICI: 0003-6951(19990816)75:7L.953:SIDH;1-5

DT Journal

TC Practical; Experimental

CY United States

LA English

L1 ANSWER 42 OF 63 INSPEC (C) 2004 IEE on STN



AN 1999:6276753 INSPEC DN A1999-15-7865K-002  
 TI Optical properties of a high-quality **insulating GaN** epilayer.  
 AU Zeng, K.C.; Lin, J.Y.; Jiang, H.X. (Dept. of Phys., Kansas State Univ.,  
 Manhattan, KS, USA); Wei Yang  
 SO Applied Physics Letters (21 June 1999) vol.74, no.25, p.3821-3. 14 refs.  
 Doc. No.: S0003-6951(99)04025-5  
 Published by: AIP  
 Price: CCCC 0003-6951/99/74(25)/3821(3)/\$15.00  
 CODEN: APPLAB ISSN: 0003-6951  
 SICI: 0003-6951(19990621)74:25L:3821:OPHQ;1-G  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L1 ANSWER 43 OF 63 INSPEC (C) 2004 IEE on STN



AN 1999:6254375 INSPEC DN A1999-13-6150C-001; B1999-07-0510-001  
 TI Near defect free GaN substrates.  
 AU Porowski, S. (High Pressure Res. Center, Polish Acad. of Sci., Warsaw,  
 Poland)  
 SO MRS Internet Journal of Nitride Semiconductor Research (1999) vol.4S1. 37  
 refs.  
 Collection URL: <http://nsr.mii.mrs.org/>  
 Published by: Mater. Res. Soc  
 CODEN: MIJNF7 ISSN: 1092-5783  
 DT Journal  
 TC General Review; Experimental  
 CY United States  
 LA English

L1 ANSWER 44 OF 63 INSPEC (C) 2004 IEE on STN



AN 1999:6156537 INSPEC DN A1999-06-7865K-008; B1999-03-2530C-038  
 TI Dynamics of fundamental optical transitions in group III-nitrides.  
 AU Jiang, H.X.; Lin, J.Y. (Dept. of Phys., Kansas State Univ., Manhattan, KS,  
 USA)  
 SO Proceedings of the SPIE - The International Society for Optical  
 Engineering (1998) vol.3277, p.108-18. 19 refs.  
 Published by: SPIE-Int. Soc. Opt. Eng  
 Price: CCCC 0277-786X/98/\$10.00  
 CODEN: PSISDG ISSN: 0277-786X  
 SICI: 0277-786X(1998)3277L:108:DFOT;1-Y  
 Conference: Ultrafast Phenomena in Semiconductors II. San Jose, CA, USA,  
 28-29 Jan 1998  
 Sponsor(s): SPIE  
 DT Conference Article; Journal

TC Experimental  
CY United States  
LA English

L1 ANSWER 45 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 1998:6015588 INSPEC DN A9820-7320-027; B9810-2520D-014  
TI Magnetic resonance of dopants and defects in GaN-based materials and devices.  
AU Carlos, W.E. (Naval Res. Lab., Washington, DC, USA)  
S0 7th International Conference on Shallow-Level Centers in Semiconductors  
Editor(s): Ammerlaan, C.A.J.; Pajot, B.  
Singapore: World Scientific, 1997. p.13-23 of xviii+534 pp. 37 refs.  
Conference: Amsterdam, Netherlands, 17-19 July 1996  
Sponsor(s): Found. Phys.; Found. Fundamental Res. Matter; Philips Res.;  
Int. Sci. Found.; Univ. Amsterdam  
ISBN: 981-02-2928-3  
DT Conference Article  
TC Experimental  
CY Singapore  
LA English

L1 ANSWER 46 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 1998:5907712 INSPEC DN A9812-7360F-001; B9806-2520D-027  
TI Deep centers in n-GaN grown by reactive molecular beam epitaxy.  
AU Fang, Z.-Q.; Look, D.C. (Res. Center, Wright State Univ., Dayton, OH, USA); Kim, W.; Fan, Z.; Botchkarev, A.; Morkoc, H.  
S0 Applied Physics Letters (4 May 1998) vol.72, no.18, p.2277-9. 10 refs.  
Doc. No.: S0003-6951(98)02818-6  
Published by: AIP  
Price: CCCC 0003-6951/98/72(18)/2277(3)/\$15.00  
CODEN: APPLAB ISSN: 0003-6951  
SICI: 0003-6951(19980504)72:18L.2277:DCGR;1-G  
DT Journal  
TC Experimental  
CY United States  
LA English

L1 ANSWER 47 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 1998:5808269 INSPEC DN A9804-7855-045  
TI Photoluminescence of Fe-complexes in GaN.  
AU Thurian, P.; Hoffmann, A.; Eckey, L.; Maxim, P.; Heitz, R.; Broser, I.  
(Inst. fur Festkorperphys., Tech. Univ. Berlin, Germany); Pressel, K.;  
Meyer, B.-K.; Schneider, J.; Bauer, J.; Kunzer, M.  
S0 III-V Nitrides. Symposium  
Editor(s): Ponce, F.A.; Moustakas, T.D.; Akasaki, I.; Monemar, B.A.

Pittsburgh, PA, USA: Mater. Res. Soc, 1997. p.707-12 of xxv+1251 pp. 11 refs.

Conference: Boston, MA, USA, 2-6 Dec 1996

DT Conference Article

TC Experimental

CY United States

LA English

L1 ANSWER 48 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Cited References
--------------	---------------------

AN 1998:5800812 INSPEC DN A9804-6170B-002

TI Investigation of vacancies in GaN by positron annihilation.

AU Jorgensen, L.V.; Kruseman, A.C.; Schut, H.; Van Veen, A. (Interfaculty Reactor Inst., Delft Univ. of Technol., Netherlands); Fanciulli, M.; Moustakas, T.D.

S0 III-V Nitrides. Symposium

Editor(s): Ponce, F.A.; Moustakas, T.D.; Akasaki, I.; Monemar, B.A.

Pittsburgh, PA, USA: Mater. Res. Soc, 1997. p.853-8 of xxv+1251 pp. 24 refs.

Conference: Boston, MA, USA, 2-6 Dec 1996

DT Conference Article

TC Experimental

CY United States

LA English

L1 ANSWER 49 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Cited References
--------------	---------------------

AN 1997:5780136 INSPEC DN A9802-7360F-015; B9801-2520D-079

TI Fe-related defects in GaN epilayers.

AU Thurian, P.; Heitz, R.; Eckey, L.; Maxim, P.; Kutzer, V.; Hoffmann, A.; Broser, I. (Inst. fur Festkorperphys., Tech. Univ. Berlin, Germany); Pressel, K.; Meyer, B.-K.

S0 23rd International Conference on the Physics of Semiconductors

Editor(s): Scheffler, M.; Zimmermann, R.

Singapore: World Scientific, 1996. p.2897-900 vol.4 of 4 vol. (xxxviii+xxvii+xxx+xxvi+3460) pp. 6 refs.

Conference: Berlin, Germany, 21-26 July 1996

ISBN: 981-02-2777-9

DT Conference Article

TC Experimental

CY Singapore

LA English

L1 ANSWER 50 OF 63 INSPEC (C) 2004 FIZ KARLSRUHE on STN

Full Text	Cited References
--------------	---------------------

AN 1997:5676103 INSPEC DN A9719-7865-063; B9710-0510D-089

TI Electrical and optical properties of semi-insulating GaN.

AU Look, D.C.; Reynolds, D.C. (Res. Center, Wright State Univ., Dayton, OH,

USA); Jones, R.L.; Kim, W.; Aktas, Oe.; Botchkarev, A.; Salvador, A.; Morkoc, H.

S0 Materials Science & Engineering B (Solid-State Materials for Advanced Technology) (Feb. 1997) vol.44, no.1-3, p.423-6. 20 refs.  
Published by: Elsevier  
Price: CCCC 0921-5107/97/\$17.00  
CODEN: MSBTEK ISSN: 0921-5107  
SICI: 0921-5107(199702)44:1/3L.423:E0PS;1-V  
Conference: 3rd International Workshop on Expert Evaluation and Control of Compound Semiconductor Materials and Technologies. Freiburg, Germany, 12-15 May 1996  
Sponsor(s): Deutsche Forschungsgemeinschaft; Fraunhofer IAF; Freiburger Compound Mater.; et al  
DT Conference Article; Journal  
TC Experimental  
CY Switzerland  
LA English

L1 ANSWER 51 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 1997:5598632 INSPEC DN B9707-1350F-018  
TI Bias dependent microwave performance of AlGaIn/GaN MODFET's up to 100 V.  
AU Wu, Y.-F.; Keller, S.; Kozodoy, P.; Keller, B.P.; Parikh, P.; Kapolnek, D.; Denbaars, S.P.; Mishra, U.K. (Dept. of Electr. & Comput. Eng., California Univ., Santa Barbara, CA, USA)  
S0 IEEE Electron Device Letters (June 1997) vol.18, no.6, p.290-2. 8 refs.  
Published by: IEEE  
Price: CCCC 0741-3106/97/\$10.00  
CODEN: EDLEDZ ISSN: 0741-3106  
SICI: 0741-3106(199706)18:6L.290:BDMP;1-X  
DT Journal  
TC Practical; Experimental  
CY United States  
LA English

L1 ANSWER 52 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 1997:5581086 INSPEC DN A9712-6170T-008; B9706-2550B-035  
TI Ion implantation doping of OMCVD grown GaN.  
AU Edwards, A.; Rao, M.V. (Dept. of Electr. & Comput. Eng., George Mason Univ., Fairfax, VA, USA); Molnar, B.; Wickenden, A.E.; Holland, O.W.; Chi, P.H.  
S0 Journal of Electronic Materials (March 1997) vol.26, no.3, p.334-9. 34 refs.  
Published by: TMS  
CODEN: JECMA5 ISSN: 0361-5235  
SICI: 0361-5235(199703)26:3L.334:IDOG;1-C  
Conference: Proceedings of the 38th Electronic Materials Conference. Santa Barbara, CA, USA, 26-28 June 1996

DT Conference Article; Journal  
TC Experimental  
CY United States  
LA English

L1 ANSWER 53 OF 63 INSPEC (C) 2004 FIZ KARLSRUHE on STN

[Full Text](#) [References](#)

AN 1997:5555400 INSPEC DN A9710-7360F-009; B9705-2520D-087  
TI Characterization of GaN using thermally stimulated current and photocurrent spectroscopies and its application to UV detectors.  
AU Huang, Z.C. (Hughes STX Corp., Greenbelt, MD, USA); Chen, J.C.; Wickenden, D.  
S0 Journal of Crystal Growth (Jan. 1997) vol.170, no.1-4, p.362-6. 12 refs.  
Doc. No.: S0022-0248(96)00576-3  
Published by: Elsevier  
Price: CCCC 0022-0248/97/\$17.00  
CODEN: JCRGAE ISSN: 0022-0248  
SICI: 0022-0248(199701)170:1/4L.362:CUTS;1-9  
Conference: 8th International Conference on Metalorganic Vapour Phase Epitaxy. Cardiff, UK, 9-13 June 1996  
DT Conference Article; Journal  
TC Experimental  
CY Netherlands  
LA English

L1 ANSWER 54 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 1997:5550853 INSPEC DN A9710-7855-018; B9705-2520D-074  
TI Excited states of Fe<sup>3+</sup> in GaN.  
AU Heitz, R.; Maxim, P.; Eckey, L.; Thurian, P.; Hoffmann, A.; Broser, I. (Inst. fur Festkorperphys., Tech. Univ. Berlin, Germany); Pressel, K.; Meyer, B.K.  
S0 Physical Review B (Condensed Matter) (15 Feb. 1997) vol.55, no.7, p.4382-7. 43 refs.  
Doc. No.: S0163-1829(97)00807-2  
Published by: APS through AIP  
Price: CCCC 0163-1829/97/55(7)/4382(6)/\$10.00  
CODEN: PRBMDO ISSN: 0163-1829  
SICI: 0163-1829(19970215)55:7L.4382:ES;1-M  
DT Journal  
TC Experimental  
CY United States  
LA English

L1 ANSWER 55 OF 63 INSPEC (C) 2004 IEE on STN

[Full Text](#) [References](#)

AN 1996:5472856 INSPEC DN A9704-7155-012  
TI Deep states in GaN studied by thermally stimulated current spectroscopy.



AU Huang, Z.C. (Hughes STX Corp., Greenbelt, MD, USA); Chen, J.C.; Mott, D.B.  
 SO Gallium Nitride and Related Materials. First International Symposium  
 Editor(s): Ponce, F.A.; Dupuis, R.D.; Nakamura, S.; Edmond, J.A.  
 Pittsburgh, PA, USA: Mater. Res. Soc, 1996. p.703-8 of xxi+970 pp. 13  
 refs.  
 Conference: Boston, MA, USA, 27 Nov-1 Dec 1995  
 DT Conference Article  
 TC Experimental  
 CY United States  
 LA English

L1 ANSWER 56 OF 63 INSPEC (C) 2004 IEE on STN



AN 1996:5311100 INSPEC DN A9616-7155-003; B9608-2520D-136  
 TI Thermally stimulated current trap in GaN.  
 AU Look, D.C.; Fang, Z.-Q. (Res. Center, Wright State Univ., Dayton, OH, USA); Kim, W.; Aktas, O.; Botchkarev, A.; Salvador, A.; Morkoc, H.  
 SO Applied Physics Letters (24 June 1996) vol.68, no.26, p.3775-7. 15 refs.  
 Doc. No.: S0003-6951(96)02826-4  
 Published by: AIP  
 Price: CCCC 0003-6951/96/68(26)/3775/3/\$10.00  
 CODEN: APPLAB ISSN: 0003-6951  
 SIC1: 0003-6951(19960624)68:26L.3775:TSCT;1-T  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L1 ANSWER 57 OF 63 INSPEC (C) 2004 IEE on STN



AN 1996:5238653 INSPEC DN A9610-0762-010; B9605-7230C-032  
 TI Photoconducting ultraviolet detectors based on GaN films grown by electron cyclotron resonance molecular beam epitaxy.  
 AU Misra, M. (Radiation Monitoring Devices Inc., Watertown, MA, USA); Moustakas, T.D.; Vaudo, R.P.; Singh, R.; Shah, K.S.  
 SO Proceedings of the SPIE - The International Society for Optical Engineering (1995) vol.2519, p.78-86. 10 refs.  
 Published by: SPIE-Int. Soc. Opt. Eng  
 Price: CCCC 0 8194 1878 1/95/\$6.00  
 CODEN: PSISDG ISSN: 0277-786X  
 SIC1: 0277-786X(1995)2519L.78:PUBD;1-Z  
 Conference: X-Ray and Ultraviolet Sensors and Applications. San Diego, CA, USA, 13-14 July 1995  
 Sponsor(s): SPIE  
 DT Conference Article; Journal  
 TC Experimental  
 CY United States  
 LA English

L1 ANSWER 58 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	References
--------------	------------

AN 1992:4145231 INSPEC DN A9212-8115G-001; B9206-0510D-116  
 TI Atomic layer epitaxy of GaN over sapphire using switched metalorganic chemical vapor deposition.  
 AU Khan, M. A. ; Skogman, R. A. ; Van Hove, J. M. ; Olson, D. T. ; Kuznia, J. N. (APA Opt. Inc., Blaine, MN, USA)  
 SO Applied Physics Letters (16 March 1992) vol.60, no.11, p.1366-8. 9 refs.  
 Price: CCCC 0003-6951/92/111366-03\$03.00  
 CODEN: APPLAB ISSN: 0003-6951  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L1 ANSWER 59 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	References
--------------	------------

AN 1982:1802623 INSPEC DN A82013422; B82009757  
 TI Dielectric properties of reactively sputtered gallium nitride-films.  
 AU Lakshmi, E. (Dept. of Phys., Indian Inst. of Technol., Delhi, New Delhi, India)  
 SO Thin Solid Films (4 Sept. 1981) vol.83, no.1, p.L137-9. 3 refs.  
 CODEN: THSFAP ISSN: 0040-6090  
 DT Journal  
 TC Experimental  
 CY Switzerland  
 LA English

L1 ANSWER 60 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	References
--------------	------------

AN 1976:932411 INSPEC DN A76062370; B76028430  
 TI Optimized growth conditions and properties of n-type and **insulating GaN**.  
 AU Jacob, G. ; Madar, R. ; Hallais, J. (Lab. d'Electronique et de Phys. Appl., Limeil-Brevannes, France)  
 SO Materials Research Bulletin (April 1976) vol.11, no.4, p.445-50. 9 refs.  
 CODEN: MRBUAC ISSN: 0025-5408  
 DT Journal  
 TC Experimental  
 CY United States  
 LA English

L1 ANSWER 61 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	References
--------------	------------

AN 1975:817993 INSPEC DN B75037918  
 TI Electroluminescent semiconductor display.  
 AU Pankove, J. I.  
 CS RCA

PI USA 3864592 4 Feb. 1975  
AD 22 March 1973  
DT Patent  
TC Practical  
CY United States  
LA English

L1 ANSWER 62 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Citing References
--------------	----------------------

AN 1974:688105 INSPEC DN A74073235  
TI Photoemission from GaN.  
AU Pankove, J. I.; Schade, H. (RCA Labs., Princeton, NJ, USA)  
SO Applied Physics Letters (1 July 1974) vol.25, no.1, p.53-5. 8 refs.  
CODEN: APPLAB ISSN: 0003-6951  
DT Journal  
TC Experimental  
CY United States  
LA English

L1 ANSWER 63 OF 63 INSPEC (C) 2004 IEE on STN

Full Text	Citing References
--------------	----------------------

AN 1974:582796 INSPEC DN A74001414  
TI Luminescence of insulating Be-doped and Li-doped GaN.  
AU Pankove, J. I.; Duffy, M. T.; Miller, E. A.; Berkeyheiser, J. E. (RCA Labs., Princeton, NJ, USA)  
SO Journal of Luminescence (Sept. 1973) vol.8, no.1, p.89-93. 12 refs.  
CODEN: JLUMA8 ISSN: 0022-2313  
DT Journal  
TC Experimental  
CY Netherlands  
LA English

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